

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): UCHIDA, et al.

Filed: February 26, 2002

For: POLISHING MEDIUM FOR CHEMICAL-MECHANICAL
POLISHING, AND POLISHING METHOD

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

February 26, 2002

Sir:

The following preliminary amendments and remarks are respectfully
submitted in connection with the above-identified application.

IN THE SPECIFICATION

Please delete the paragraph on page 10, lines 5-11, and substitute therefor
the following new paragraph:

--From the results of an experiment made by the present inventors, it is
known that the coefficient of kinetic friction between a metal film and a metal
polishing cloth via the polishing medium for CMP comes to less than 0.25 when
the content of the protective-film-forming agent in 100 g of the metal polishing
medium without containing the water-soluble polymer is in a range of 0.0001